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(54) Title: MAGNETIC STRUCTURE IN SEMICONDUCTOR DEVICE, AND SEMICONDUCTOR DEVICE

(54) 发明名称: 半导体设备中的磁性结构以及半导体设备

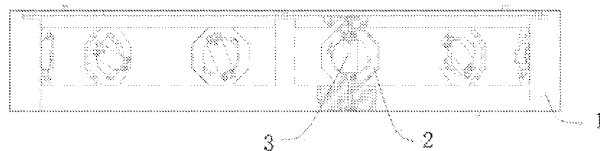


图 3

(57) Abstract: Disclosed are a magnetic structure in a semiconductor device, and the semiconductor device. The magnetic structure is arranged outside a reaction chamber of the semiconductor device in a surrounding manner, and comprises: an annular support member, a plurality of angle adjustment assemblies, and a plurality of magnetic members, wherein the annular support member is arranged surrounding the reaction chamber of the semiconductor device; the plurality of angle adjustment assemblies are connected to the annular support member and are distributed in the circumferential direction of the annular support member; the magnetic members are correspondingly connected to the angle adjustment assemblies on a one-to-one basis; and each of the angle adjustment assemblies can fix the corresponding magnetic member on the annular support member and is used for adjusting the direction of the magnetic line of force of the magnetic member and the included angle between the magnetic line of force of the magnetic member and the axis of the reaction chamber. The magnetic structure in a semiconductor device and the semiconductor device disclosed in the present invention can not only improve the process results, but also meet different process requirements.

(57) 摘要: 本发明公开一种半导体设备中的磁性结构以及半导体设备, 磁性结构磁性结构环绕设置于半导体设备的反应腔室的外部, 磁性结构包括: 环形支撑件、多个角度调节组件和多个磁性件; 其中, 环形支撑件环绕半导体设备的反应腔室设置; 多个角度调节组件与环形支撑件连接, 且沿环形支撑件的周向分布; 各个磁性件一一对应地与各个角度调节组件连接; 角度调节组件能够将对应的磁性件固定在环形支撑件上, 且用于调节磁性件的磁力线方向以及磁性件的磁力线与反应腔室的轴线之间的夹角的大小。本发明公开的半导体设备中的磁性结构以及半导体设备, 既可以改善工艺结果, 又可以满足不同的工艺需求。

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